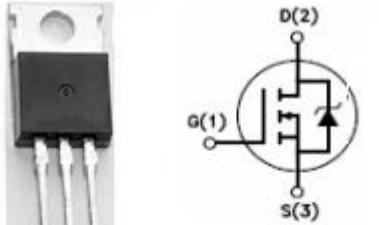


**isc N-Channel MOSFET Transistor****15N12****• FEATURES**

- Drain Current  $I_D = 15A @ T_c=25^\circ C$
- Drain Source Voltage :  $V_{DSS} = 120V$ (Min)
- Static Drain-Source On-Resistance :  $R_{DS(on)} = 0.15 \Omega$  (Max)
- Fast Switching
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



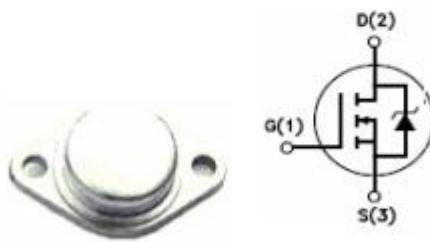
PIN 1.Gate  
2.Drain  
3.Source

**• APPLICATIONS**

- Switching regulators
- Switching converters,motor drivers,relay drivers.

**• ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ C$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{DSS}$	Drain-Source Voltage	120	V
$V_{GS}$	Gate-Source Voltage-Continuous	$\pm 30$	V
$I_D$	Drain Current-Continuous	15	A
$I_{DM}$	Drain Current-Single Plused	40	A
$P_D$	Total Dissipation @ $T_c=25^\circ C$	100	W
$T_j$	Max. Operating Junction Temperature	150	°C
$T_{stg}$	Storage Temperature	-55~150	°C



PIN 1.Gate  
2.Drain  
3.Source

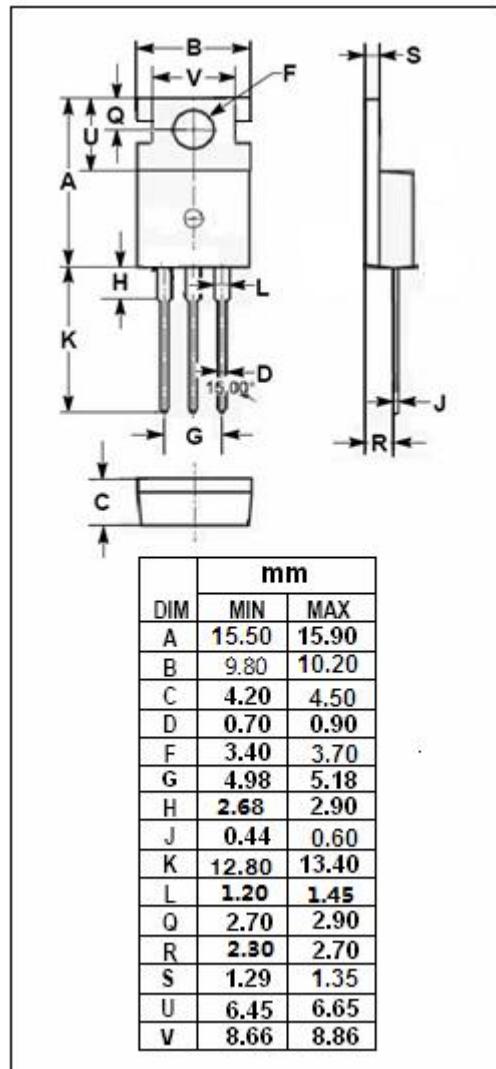
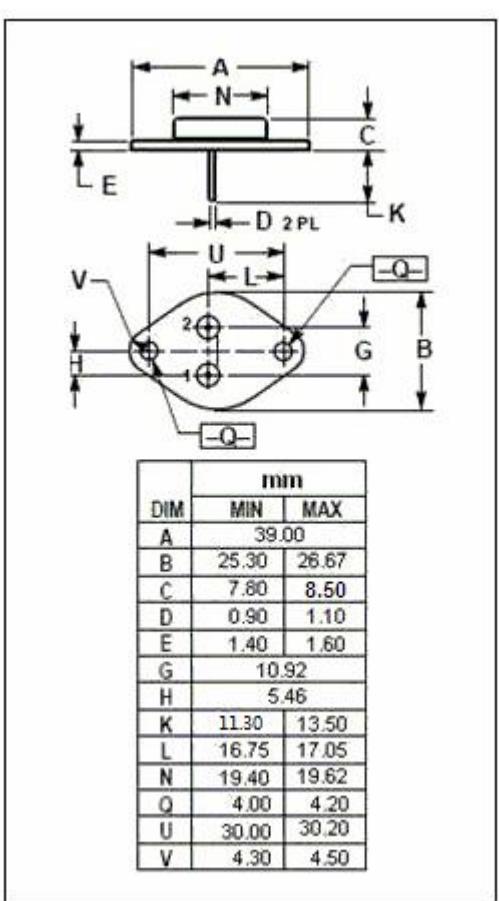
**isc N-Channel MOSFET Transistor****15N12****• ELECTRICAL CHARACTERISTICS****T<sub>C</sub>=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0; I <sub>D</sub> =1mA	120			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> =1mA	2.0		4.0	V
V <sub>SD</sub>	Diode Forward On-voltage	I <sub>S</sub> = 7.5A ;V <sub>GS</sub> = 0			1.4	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> = 7.5A			0.15	Ω
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> = ±20V;V <sub>DS</sub> = 0			±100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =120V; V <sub>GS</sub> = 0			1	μA
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =25V; V <sub>GS</sub> =0V; f <sub>T</sub> =1MHz			1700	pF
C <sub>rss</sub>	Reverse Transfer capacitance				350	
C <sub>oss</sub>	Output Capacitance				750	
t <sub>r</sub>	Rise Time	V <sub>GS</sub> =10V; I <sub>D</sub> =7.5A; V <sub>DD</sub> =75V; R <sub>GS</sub> =50 Ω			150	ns
t <sub>d(on)</sub>	Turn-on Delay Time				50	
t <sub>f</sub>	Fall Time				125	
t <sub>d(off)</sub>	Turn-off Delay Time				185	
					225	
					75	
					190	

## isc N-Channel MOSFET Transistor

15N12

## Outline Drawing



## NOTICE:

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